

INCH-POUND

MIL-PRF-19500/643
18 April 1997

PERFORMANCE SPECIFICATION

SEMICONDUCTOR DEVICE, DIODE, SILICON,
POWER RECTIFIER, DUAL, COMMON CATHODE OR ANODE CENTER TAP, ULTRAFAST,
TYPES 1N6766 THROUGH 1N6767 AND 1N6767R THROUGH 1N6767R
JANTX, JANTXV, and JANS

This specification is approved for use by all Departments and Agencies of the Department of Defense.

1. SCOPE

1.1 Scope. This specification covers the detail requirements for silicon, dual ultrafast, power rectifier diodes in a center-tap configuration. Three levels of product assurance are provided for each device type as specified in MIL-PRF-19500.

1.2 Physical dimensions. See figure 1 (similar to T0-254AA, isolated).

1.3 Maximum ratings.

Types	V_{RWM} 1/ $I_D = 10 \mu A$ dc	I_F 1/ 2/ $T_C = +100^\circ C$	I_{FSM} 1/ $t_p = 8.3$ ms	$R_{\theta JC}$ 1/	$R_{\theta JA}$ 1/	T_{STG} and T_{OP}
	V dc	A dc	A(pk)	$^\circ C/W$	$^\circ C/W$	$^\circ C$
1N6766, 1N6766R 1N6767, 1N6767R	400 600	12	125	1.8	40	-65 to +150

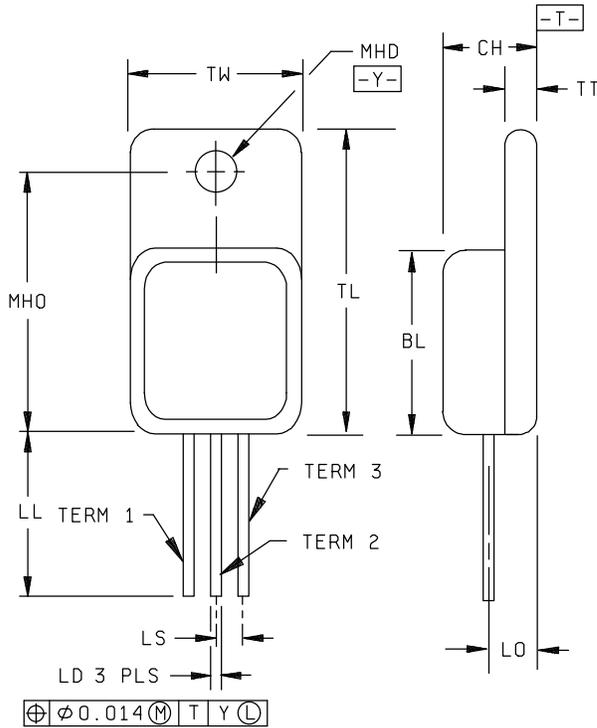
1/ Each individual diode.

2/ Derate at 240 mA/ $^\circ C$ above $T_C = +100^\circ C$.

1.4 Primary electrical characteristics. Unless otherwise specified, primary electrical characteristics are at +25 $^\circ C$, and per diode.

Types	V_{F1} $I_F = 6$ A dc	V_{F2} $I_F = 12$ A dc	I_{R1} $V_R = 0.8 V_{RWM}$ (See 1.3)	I_{R2} $V_R = 0.8 V_{RWM}$ (See 1.3) $T_C = +100^\circ C$	t_{rr}	C_J $V_R = 5$ V $f = 1$ MHz
	V dc	V dc	μA dc	μA dc	ns	pF
1N6766, 1N6766R 1N6767, 1N6767R	1.35	1.55	10	1,000	60	300

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Commander, Defense Supply Center, Columbus, ATTN: DSCC-VA, 3990 East Broad Street, Columbus, Ohio 43216-5000, by using the Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.



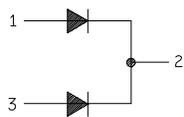
Dimensions				
Symbol	Inches		Millimeters	
	Min	Max	Min	Max
BL	0.535	0.545	13.59	13.84
CH	0.249	0.260	6.32	6.60
LD	0.035	0.045	0.89	1.14
LL	0.510	0.550	12.95	13.97
LO	0.150 typ		3.81 typ	
LS	0.150 bsc		3.81 bsc	
MHD	0.139	0.149	3.53	3.78
MHO	0.665	0.685	16.89	17.40
TL	0.790	0.800	20.07	20.32
TT	0.040	0.050	1.02	1.27
TW	0.535	0.545	13.54	13.84

NOTES:

1. Dimensions are in inches.
2. Metric equivalents are given for general information only. See 3.3.
3. All terminals are isolated from case.

SCHEMATIC

1N6766, 1N6767

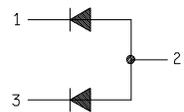


Terminal

Description

- | | |
|---|---------|
| 1 | Anode 1 |
| 2 | Cathode |
| 3 | Anode 2 |

1N6766R, 1N6767R



Terminal

Description

- | | |
|---|-----------|
| 1 | Cathode 1 |
| 2 | Anode |
| 3 | Cathode 2 |

FIGURE 1. Physical dimensions and configuration (T0-254AA).

2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3 and 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements documents cited in sections 3 and 4 of this specification, whether or not they are listed.

2.1.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DODISS) and supplement thereto, cited in the solicitation (see 6.2).

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-19500 - Semiconductor Devices, General Specification for.

STANDARD

MILITARY

MIL-STD-750 - Test Methods for Semiconductor Devices.

(Unless otherwise indicated, copies of federal and military specifications, standards, and handbooks are available from the Standardization Documents Order Desk, Building 4D, 700 Robbins Avenue, Philadelphia, PA 19111-5094.)

2.2 Order of precedence. In the event of a conflict between the text of this document and the references cited herein (except for related associated specifications or specification sheets), the text of this document shall take precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Associated detail specification. The individual item requirements shall be in accordance with MIL-PRF-19500 and as specified herein.

3.2 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500.

3.3 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-19500 and on figure 1. Methods used for electrical isolation of the terminal feedthroughs shall employ materials that contain a minimum of 90 percent Al_2O_3 (ceramic). Examples of such construction techniques are metallized ceramic eyelets or ceramic walled packages. The preferred measurements used herein is the metric SI system. However, since this item was originally designed using inch-pound units of measurement, in the event of a conflict between the metric and inch-pound units, the inch-pound units shall take precedence.

3.3.1 Lead material and finish. Lead finish shall be solderable in accordance with MIL-PRF-19500, MIL-STD-750, and herein. Where a choice of lead finish or formation is desired, it shall be specified in the acquisition document (see 6.2). When lead formation is performed, as a minimum, the vendor shall perform 100 percent hermetic seal in accordance with screen 14 of table II of MIL-PRF-19500 and 100 percent DC testing in accordance with group A, subgroup 2 herein.

3.3.2 Polarity. Polarity and terminal configuration shall be in accordance with figure 1 herein.

3.4 Marking. Marking shall be in accordance with MIL-PRF-19500.

4. QUALITY ASSURANCE PROVISIONS

4.1 Sampling and inspection. Sampling and inspection shall be in accordance with MIL-PRF-19500, and as specified herein.

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500, and table III herein.

4.3 Screening (JANTX, JANTXV, and JANS levels). Screening shall be in accordance with table IV of MIL-PRF-19500, and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see table IV of MIL-PRF-19500)	Measurement	
	JANS level	JANTX and JANTXV levels
3C 1/	Thermal impedance (see 4.3.2)	Thermal impedance (see 4.3.2)
9 and 10	Not applicable	Not applicable
11	I_{R1} and V_{F2}	I_{R1} and V_{F2}
12	See 4.3.1, $t = 120$ hours	See 4.3.1, $t = 48$ hours
13	Subgroups 2 and 3 of table I herein; V_{F2} and I_{R1} ; $\Delta I_{R1} \leq 100$ percent of initial value or $\pm 2.5\mu A$, whichever is greater; $\Delta V_{F2} \leq \pm 100$ mV.	Subgroup 2 of table I herein; V_{F2} and I_{R1} ; $\Delta I_{R1} \leq 100$ percent of initial value or $\pm 2.5\mu A$ whichever is greater; $\Delta V_{F2} \leq \pm 100$ mV.

1/ Thermal impedance shall be performed any time before screen 13.

4.3.1 Power burn-in conditions. Power burn-in conditions are as follows:

MIL-STD-750 method 1038, test condition A. $T_C = +125^\circ C$; $V_R = 0.8$ of rated V_{RWM} (see 1.3).

4.3.2 Thermal impedance ($Z_{\theta JX}$) measurements for screening. The $Z_{\theta JX}$ measurements shall be performed in accordance with MIL-STD-750, method 3101. Test each die separately. The maximum limit (not to exceed the group A, subgroup 2 limit) and conditions for $Z_{\theta JX}$ in screening (table IV of MIL-PRF-19500) shall be derived by each vendor by means of statistical process control. When the process has exhibited control and capability, the capability data shall be used to establish the fixed screening limit. In addition to screening, once a fixed limit has been established, monitor all future sealing lots using a random five piece sample from each lot to be plotted on the applicable X, R chart. If a lot exhibits an out of control condition, the entire lot shall be removed from the line and held for Engineering evaluation and disposition.

4.3.2.1 Thermal impedance ($Z_{\theta JX}$) measurements for initial qualification or requalification. The $Z_{\theta JX}$ measurements shall be performed in accordance with MIL-STD-750, method 3101 (read and record data $Z_{\theta JX}$). Derived conditions limits and thermal response curve shall be supplied to the qualifying activity on the qualification lot prior to qualification approval. Measurement conditions shall be in accordance with 4.4.1.

4.4 Quality conformance inspection. Quality conformance inspection shall be in accordance with MIL-PRF-19500 and as specified herein.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with MIL-PRF-19500 and table I herein. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps of table II herein. The following test conditions shall be used for $Z_{\theta JX}$, group A inspection:

- a. I_M measure current ----- 15 mA
- b. I_H forward heating current ----- 10-50 A
- c. t_H heating time ----- 200 ms
- d. t_{MD} measurement delay time ----- 35 μ s
- e. V_H heating voltage ----- 1 V

The maximum limit for $Z_{\theta JX}$ under these conditions are $Z_{\theta JX}(\max) = 1.6^\circ\text{C/W}$

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VIa (JANS) and table VIb (JANTX and JANTXV) of MIL-PRF-19500 and as follows. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps of table II herein.

4.4.2.1 Group B inspection, table VIa (JANS) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
4	1037	I_F or $I_O = 1.25$ A to 10 A; $\Delta T_J = +85^\circ\text{C}$ minimum, for 2,000 cycles minimum.

4.4.2.2 Group B inspection, table VIb (JANTX and JANTXV) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
3	1037	I_F or $I_O = 1.25$ A to 10 A; $\Delta T_J = +85^\circ\text{C}$ minimum, for 2,000 cycles minimum.

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VII of MIL-PRF-19500 and as follows. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps of table II herein.

4.4.3.1 Group C inspection, table VII of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
2	2036	Test condition A, 5 pounds, $t = 15$ seconds ± 3 seconds.
6	1037	I_F or $I_O = 1.25$ A to 10 A; $\Delta T_J = +85^\circ\text{C}$ minimum, for 6,000 cycles minimum.

4.4.4 Group E inspection. Group E inspection shall be conducted in accordance with the conditions specified for subgroup testing in table III herein. Electrical measurements (end points) and delta requirements shall be in accordance with the applicable steps and footnotes of table II herein.

4.5 Methods of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

TABLE I. Group A inspection. 1/ 2/

Inspection	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical examination	2071					
<u>Subgroup 2</u>						
Thermal impedance <u>3/</u>	3101	See 4.4.1	$Z_{\theta JX}$		1.6	°C/W
Breakdown voltage 1N6766, 1N6766R 1N6767, 1N6767R	4022	$I_R = 10 \mu\text{A}$ dc, pulsed <u>4/</u>	V_{BR}	400 600		V dc V dc
Forward voltage	4011	$I_F = 6 \text{ A}$ dc, pulsed <u>4/</u> $I_F = 12 \text{ A}$ dc, pulsed <u>4/</u>	V_{F1} V_{F2}		1.35 1.55	V dc V dc
Reverse leakage current	4016	DC method; pulsed <u>4/</u> $V_R = 0.8$ of V_{RWM} (see 1.3)	I_{R1}		10	μA dc
<u>Subgroup 3</u>						
High temperature operation:		$T_C = +100^\circ\text{C}$				
Reverse leakage current	4016	DC method; pulsed <u>4/</u> $V_R = 0.8$ of V_{RWM} (see 1.3)	I_{R2}		1.0	mA dc
Low-temperature operation:		$T_A = -55^\circ\text{C}$				
Forward voltage	4011	$I_F = 12 \text{ A}$ dc, pulsed <u>4/</u>	V_{F3}		1.70	V dc
<u>Subgroup 4</u>						
Scope display evaluation <u>5/</u>	4023					
Reverse recovery time measurements	4031	Condition B; $I_F = 1.0 \text{ A}$, $di/dt = 50 \text{ A}/\mu\text{s}$	t_{rr}		60	ns
<u>Subgroups 5 and 6</u>						
Not applicable						
<u>Subgroup 7</u>						
Junction capacitance	4001	$V_R = 5 \text{ V}$ dc; $f = 1.0 \text{ MHz}$	C_J		300	pF

1/ For sampling plan, see MIL-PRF-19500.

2/ Each individual diode.

3/ If 4.4.1 test conditions are performed in 100 percent screening, this test need not be performed in Group A.

4/ Pulse test: pulse width = 300 μs , duty cycle ≤ 2 percent.

5/ The reverse breakdown characteristics shall be viewed on an oscilloscope with display calibration factors of 50 to 100 $\mu\text{A}/\text{division}$ and 50 to 100 $\text{V}/\text{division}$. Reverse current over the knee shall be at least 500 μA . Each device may exhibit a slightly rounded characteristic and any discontinuity or dynamic instability of the trace shall be cause for rejection.

TABLE II. Groups A, B, C, and E electrical measurements. 1/ 2/ 3/

MIL-PRF-19500/643

Step	Inspection	MIL-STD-750		Symbol	Limits		Unit
		Method	Conditions		Min	Max	
1	Forward voltage	4011	$I_F = 12$ A dc pulsed	V_{F2}		1.55	V dc
2	Reverse leakage current	4016	$V_R = 0.8$ of V_{RWM} (see 1.3) DC method, pulsed	I_{R1}		10	μ A dc
3	Forward voltage	4011	$I_F = 12$ A dc pulsed	ΔV_{F2}		± 100 mV dc from initial reading	
4	Reverse leakage current	4016	$V_R = 0.8$ of V_{RWM} (see 1.3) DC method, pulsed	ΔI_{R1}		100 percent of initial value or ± 2.5 μ A dc whichever is greater.	
5	Thermal impedance	3101	See 4.4.1	$Z_{\theta JX}$		1.60	$^{\circ}$ C/W

1/ The electrical measurements for table VIa (JANS) of MIL-PRF-19500 are as follows:

- a. Subgroup 3, see table II herein, steps 1 and 2.
- b. Subgroup 4, see table II herein, steps 1, 2, 3, 4, and 5.
- c. Subgroup 5, see table II herein, steps 1, 2, 3, and 4.

2/ The electrical measurements for table VIb (JANTX and JANTXV) of MIL-PRF-19500 are as follows:

- a. Subgroup 2, see table II herein, steps 1 and 2.
- a. Subgroup 3, see table II herein, steps 1, 2, and 5.
- a. Subgroup 6, see table II herein, steps 1 and 2.

3/ The electrical measurements for table VII of MIL-PRF-19500 are as follows:

- a. Subgroups 2 and 3, see table II herein, steps 1 and 2 for all levels.
- a. Subgroup 6, see table II herein, steps 1, 2, and 5 for all levels.

TABLE III. Group E inspection (all quality levels) for qualification only. 1/

Inspection	MIL-STD-750		Sampling plan
	Method	Conditions	
<u>Subgroup 1</u>			22 devices c = 0
Thermal shock (temperature cycling)	1051	500 cycles	
Hermetic seal	1071		
Fine leak		Test condition H 5×10^{-7} atm cc/s	
Gross leak		Test condition C or K	
Electrical measurements		See table II herein, steps 1 and 2	
<u>Subgroup 2</u>			22 devices c = 0
Steady-state reverse bias	1038	Test condition A t = 1,000 hours, $T_C = +125^\circ\text{C}$ $V_R = 0.8$ of rated V_{RWM} (see 1.3)	
Electrical measurements		See table II herein, steps 1 and 2	
<u>Subgroup 3</u>			3 devices c = 0
Destructive physical analysis	2101		
<u>Subgroup 4</u>			22 devices c = 0
Thermal resistance	3101	see 4.5.2; $R_{\theta JC} = 1.8^\circ\text{C/W}$	
<u>Subgroup 5</u>			15 devices c = 0
Barometric pressure (reduced)	1001	$V_R =$ rated V_{RWM} (see 1.3)	

1/ For initial design and process change verification only (one time testing).

4.5.2 Thermal resistance. Thermal resistance measurements shall be performed in accordance with method 3101 of MIL-STD-750. The maximum limits for $R_{\theta JC}$ (max) shall be 1.8°C/W for devices in the TO-254AA case style. Each diode leg shall be measured. The following parameter measurements shall apply:

- a. I_M measure current ----- 15 mA
- b. I_H forward heating current ----- 10 A - 50A
- c. t_H heating time ----- Steady state (see MIL-STD-750, method 3101)
- d. t_{MD} measurement delay time ----- 35 μ s
- e. V_H heating voltage ----- 1 V

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-19500.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory.)

6.1 Notes. The notes specified in MIL-PRF-19500 are applicable to this specification.

6.2 Acquisition requirements. Acquisition documents should specify the following:

- a. Title, number and date of the specification.
- b. Issue of DODISS to be cited in the solicitation and, if required, the specific issue of documents referenced (see 2.2.1).
- c. Lead finish or formation may be specified (see 3.3.1).
- d. Type designation and product assurance level.

6.3 Cross reference list. Parts covered by this specification may be used to replace the following commercial Part of Identifying Numbers (PIN):

Preferred types	Commercial types
JANTX1N6766, JANTX1N6766R JANTX1N6767, JANTX1N6767R	1N6766, 1N6766R 1N6767, 1N6767R
JANTXV1N6766, JANTXV1N6766R JANTXV1N6767, JANTXV1N6767R	1N6766, 1N6766R 1N6767, 1N6767R

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CONCLUDING MATERIAL

Custodians:

Army - CR
Navy - EC
Air Force - 17
NASA - NA

Review activities

Army - CR
Air Force - 17
DLA - ES

Preparing activity:
DLA - CC

(Project 5961-1889)

STANDARDIZATION DOCUMENT IMPROVEMENT PROPOSAL

INSTRUCTIONS

1. The preparing activity must complete blocks 1, 2, 3, and 8. In block 1, both the document number and revision letter should be given.
2. The submitter of this form must complete blocks 4, 5, 6, and 7.
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I RECOMMEND A CHANGE:

1. DOCUMENT NUMBER
MIL-PRF-19500/643

2. DOCUMENT DATE 1 April 1997

3. DOCUMENT TITLE

SEMICONDUCTOR DEVICE, DIODE, SILICON, POWER RECTIFIER, DUAL, COMMON CATHODE OR ANODE CENTER TAP, ULTRAFast, TYPES 1N6766 THROUGH 1N6767 AND 1N6767R THROUGH 1N6767R, JANTX, JANTXV, AND JANS

4. NATURE OF CHANGE (Identify paragraph number and include proposed rewrite, if possible. Attach extra sheets as needed.)

5. REASON FOR RECOMMENDATION

6. SUBMITTER

a. NAME (Last, First, Middle initial)

b. ORGANIZATION

c. ADDRESS (Include Zip Code)

d. TELEPHONE (Include Area Code)

7. DATE SUBMITTED
(YYMMDD)

- (1) Commercial
- (2) AUTOVON
(If applicable)

8. PREPARING ACTIVITY

a. NAME

b. TELEPHONE (Include Area Code)
(1) Commercial (2) AUTOVON

c. ADDRESS (Include Zip Code)

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